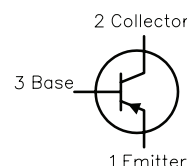
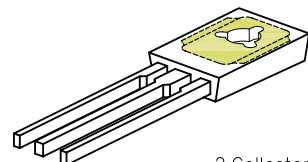




## Description:

Medium Power Plastic PNP, TO-126, Silicon Transistor. Designed for driver circuits, switching and amplifier applications.

RoHS  
Compliant



## Features:

- Low Saturation Voltage :  $V_{CE(sat)}$  0.6V DC,  $I_C = 1A$
- Excellent power dissipation due to Thermopad Construction  $P_D = 30 @ T_C = 25^\circ C$

## Absolute Maximum Ratings:

Characteristic	Symbol	Rating
Collector - Base Voltage	$V_{CBO}$	80V
Collector - Emitter Voltage	$V_{CEO}$	80V
Emitter - Base Voltage	$V_{EBO}$	5V
Continuous Collector Current	$I_C$	1A
Base Current	$I_B$	1A
Total Device Dissipation ( $T_C = +25^\circ C$ ) Derate above $25^\circ C$	$P_D$	30W 0.24mW/ $^\circ C$
Operating Junction Temperature Range	$T_J$	$-65^\circ C$ to $+150^\circ C$
Storage Temperature Range	$T_{STG}$	$-65^\circ C$ to $+150^\circ C$

## Electrical Characteristics ( $T_A = 25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min.	Max.	Unit
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### OFF Characteristics

Collector - Emitter Breakdown Voltage (Note 1)	$V_{(BR)CEO}$	$I_C = 100mA, I_B = 0$	80	-	V
Collector Cut-off Current	$I_{CEX}$	$V_{CE} = 80V, I_{EB(off)} = 1.5V$	-	0.1	mA
	$I_{CEO}$	$V_{CB} = 40V, I_B = 0$	-	0.5	mA
Collector Cut-off Current	$I_{CBO}$	$V_{EB} = 80V, I_E = 0$	-	0.1	mA
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = 5V, I_C = 0$	-	1	mA

### ON Characteristics (Note 1)

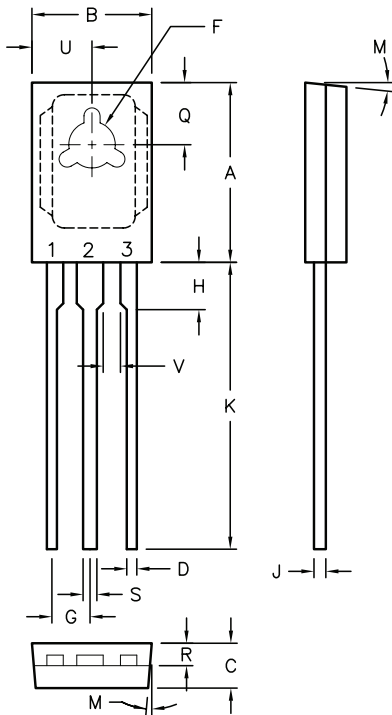
DC Current Gain	$h_{fe}$	$V_{CE} = 1V, I_C = 50mA$	40	-	-
		$V_{CE} = 1V, I_C = 1,500mA$	30	150	-
		$V_{CE} = 1V, I_C = 1A$	10	-	-

Parameter	Symbol	Test Conditions	Min.	Max.	Unit
Collector - Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 1A, I_B = 100mA$	-	0.6	V
Base - Emitter Saturation Voltage	$V_{BE(on)}$	$I_C = 1A, I_B = 1V$	-	1.3	V
	$V_{BE(sat)}$	$I_C = 1A, I_B = 100mA$	-	1.3	

### Small-Signal Characteristics

Current Gain - Bandwidth Product	$f_T$	$V_{CE} = 10V, I_C = 250mA, f = 1kHz$	3	-	MHz
Output Capacitance	$C_{OBO}$	$V_{CB} = 10V, I_E = 0, f = 100kHz$	-	100	pF
Input Impedance	$h_{fe}$	$V_{CE} = 10V, I_C = 1mA, f = 1kHz$	-	-	k $\Omega$
		$V_{CE} = 10V, I_C = 10mA, f = 1kHz$	-	-	
Small-Signal Current Gain	$h_{fe}$	$V_{CE} = 10V, I_C = 250mA, f = 1kHz$	25	-	-

**Note 1:** Pulse Test : Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$



### Pin Configuration:

1. Emitter
2. Collector
3. Base

Dim.	Min.	Max.
A	10.8	11.05
B	7.49	7.75
C	2.41	2.67
D	0.51	0.66
F	2.92	3.18
G	2.31	2.46
H	1.27	2.41
J	0.38	0.64
K	15.11	16.64
M	3° TYP	
Q	3.76	4.01
R	1.14	1.4
S	0.64	0.89
U	3.68	3.94
V	1.02	-

Dimensions : Millimetres

### Part Number Table

Description	Part Number
Bipolar Transistor, PNP, 1A, 80V, TO-126	2N4920

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